SN74AHCT244-Q1 具有三态输出的八路缓冲器/驱动器

1 特性

- 符合汽车应用要求
- ESD 保护超过 1000V（根据 MIL-STD-883 方法 3015）；超过 200V（使用机器模型，C = 200pF，R = 0）
- EPIC™（增强性能植入式 CMOS）工艺
- 输入兼容 TTL 电压

2 应用

- 启用或禁用数字信号
- 消除缓慢或嘈杂输入信号
- 在控制器复位期间保持信号
- 对开关进行去抖

3 说明

该八路缓冲器/驱动器专门设计用于提高三态存储器地址驱动器、时钟驱动器以及总线导向接收器和发送器的性能和密度。

表 3-1. 封装信息(1)

器件型号	封装(2)	封装尺寸（标称值）
SN74AHCT244-Q1	DW（SOIC，20）	12.80mm × 7.50mm
	PW（TSSOP，20）	6.5mm × 4.4mm

(1) 有关最新的封装和订购信息，请参阅本文档结尾的“封装选项附录”，或访问 TI 网站：http://www.ti.com。

(2) 封装图、热数据和符号可登录 http://www.ti.com/packaging 获取。

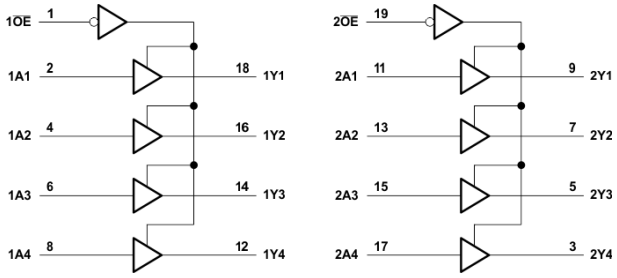


图 3-1. 逻辑图（正逻辑）

Table of Contents

4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision C (April 2008) to Revision D (April 2023)	Page
• 添加了*应用*、*封装信息* 表、*引脚功能* 表、*ESD 等级* 表、*热性能信息* 表、*器件功能模式*、*应用和实施* 部分、*电源相关建议* 部分、*布局* 部分、*器件和文档支持* 部分以及*机械、封装和可订购信息* 部分	1

5 Pin Configuration and Functions

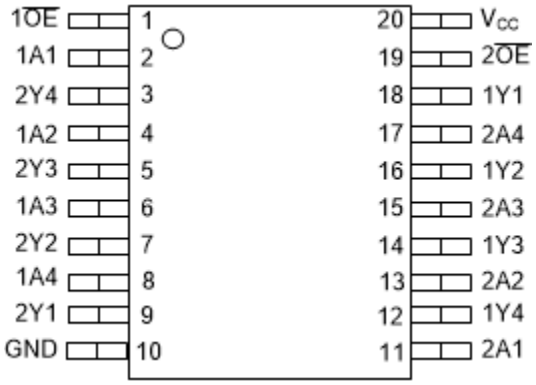


图 5-1. DW or PW Package (Top View)

表 5-1. Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	1 $\overline{OE}$	I	Output Enable 1
2	1A1	I	1A1 Input
3	2Y4	O	2Y4 Output
4	1A2	I	1A2 Input
5	2Y3	O	2Y3 Output
6	1A3	I	1A3 Input
7	2Y2	O	2Y2 Output
8	1A4	I	1A4 Input
9	2Y1	O	2Y1 Output
10	GND	—	Ground pin
11	2A1	I	2A1 Input
12	1Y4	O	1Y4 Output
13	2A2	I	2A2 Input
14	1Y3	O	1Y3 Output
15	2A3	I	2A3 Input
16	1Y2	O	1Y2 Output
17	2A4	I	2A4 Input
18	1Y1	O	1Y1 Output
19	2 $\overline{OE}$	I	Output Enable 2
20	VCC	—	Power Pin

6 Specifications

6.1 Absolute Maximum Ratings

over Operating Free-air Temperature Range (Unless Otherwise Noted)

		MIN	MAX	UNIT
V_{CC}	Supply voltage range	−0.5	7	V
V_I (1)	Input voltage range	−0.5	7	V
V_O (1)	Output voltage range	−0.5	V_{CC} + 0.5	V
I_{IK} (V_I < 0)	Input clamp current		−20	mA
I_{OK} (V_O < 0 or V_O > V_{CC})	Output clamp current		±20	mA
I_O (V_O = 0 to V_{CC})	Continuous output current		±25	mA
	Continuous current through V_{CC} or GND		±75	mA
T_{stg}	Storage temperature range	−65	150	°C

(1) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			MIN	MAX	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	0	1500	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	0	2000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

(see (Note 1))

			MIN	MAX	UNIT
V_{CC}	Supply voltage		4.5	5.5	V
V_{IH}	High-level input voltage		2		V
V_{IL}	Low-level input voltage			0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current			−8	mA
I_{OL}	Low-level output current			8	mA
T_A	Operating free-air temperature	I-suffix device	−40	85	°C
		Q-suffix device	−40	125	

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

6.4 Thermal Information

THERMAL METRIC(1)		SN74AHCT244-Q1		UNIT
		DW	PW	
		20 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	58	83	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	T_A = 25°C			MIN	MAX	UNIT
			MIN	TYP	MAX			
V_{OH}	I_{OH} = −50 mA	4.5 V	4.4	4.5		4.4		V
	I_{OH} = −8 mA		3.94			3.8		
V_{OL}	I_{OL} = 50 mA	4.5 V			0.1		0.1	V
	I_{OL} = 8 mA				0.36		0.44	
I_{OZ}	V_O = V_{CC} or GND	5.5 V			±0.25		±2.5	µA
I_I	V_I = 5.5 V or GND	0 V to 5.5 V			±0.1		±1	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	5.5 V			4		40	µA
ΔI_{CC} (1)	One input at 3.4 V, Other inputs at V_{CC} or GND	5.5 V			1.35	1.5		µA
C_i	V_I = V_{CC} or GND	5 V		2.5	10			pF
C_o	V_O = V_{CC} or GND	5 V		3				pF

(1) This is the increase in supply current for each input at one of the specified TTL voltage levels, rather than 0 V or V_{CC}.

6.6 Switching Characteristics

over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see 图 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			MIN	MAX	UNIT
				MIN	TYP	MAX			
t_{PLH}	A	Y	C_L = 15 pF		5.4	7.4	1	8.5	ns
t_{PHL}					5.4	7.4	1	8.5	
t_{PZH}	$\overline{OE}$	Y	C_L = 15 pF		7.7	10.4	1	12	ns
t_{PZL}					7.7	10.4	1	12	
t_{PHZ}	$\overline{OE}$	Y	C_L = 15 pF		5	9.4	1	10	ns
t_{PLZ}					5	9.4	1	10	
t_{PLH}	A	Y	C_L = 50 pF		5.9	8.4	1	9.5	ns
t_{PHL}					5.9	8.4	1	9.5	
t_{PZH}	$\overline{OE}$	Y	C_L = 50 pF		8.2	11.4	1	13	ns
t_{PZL}					8.2	11.4	1	13	
t_{PHZ}	$\overline{OE}$	Y	C_L = 50 pF		8.8	11.4	1	13	ns
t_{PLZ}					8.8	11.4	1	13	
$t_{sk(o)}$			C_L = 50 pF			1			ns

6.7 Noise Characteristics

V_{CC} = 5 V, C_L = 50 pF, T_A = 25°C (see (Note 1))

PARAMETER		MIN	TYP	MAX	UNIT
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		4.1		V

V_{CC} = 5 V, C_L = 50 pF, T_A = 25°C (see (Note 1))

PARAMETER		MIN	TYP	MAX	UNIT
$V_{IH(D)}$	High-level dynamic input voltage	2			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.8	V

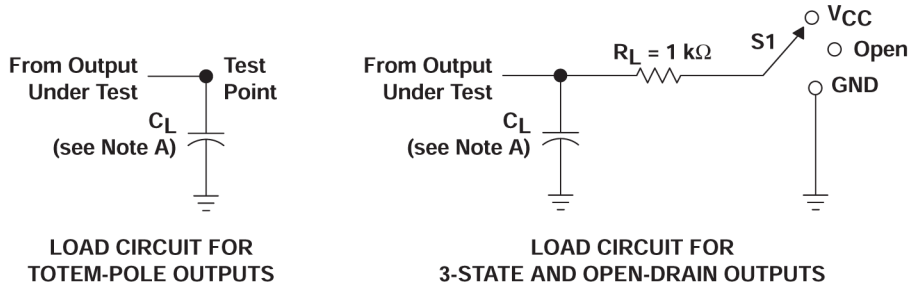
(1) Characteristics are for surface-mount packages only.

6.8 Operating Characteristics

V_{CC} = 5 V, T_A = 25°C

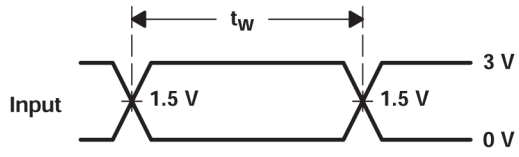
PARAMETER		TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance	No load,	f = 1 MHz	8.2	pF

7 Parameter Measurement Information

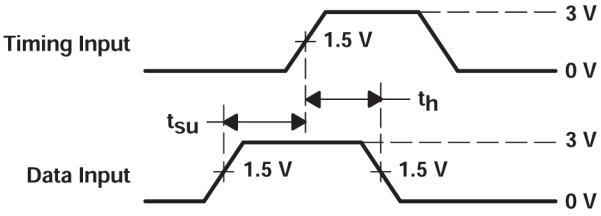


LOAD CIRCUIT FOR TOTEM-POLE OUTPUTS

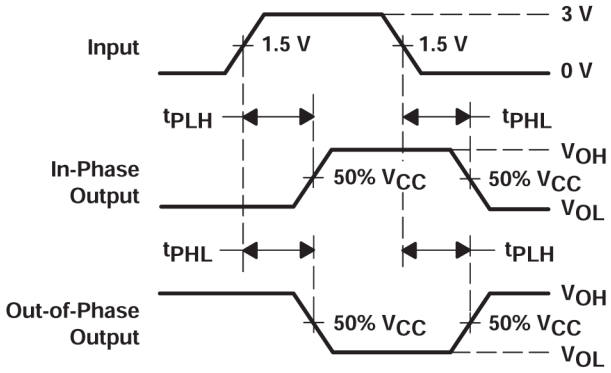
LOAD CIRCUIT FOR 3-STATE AND OPEN-DRAIN OUTPUTS



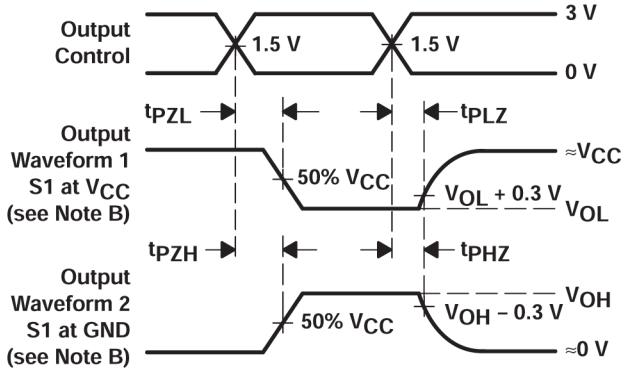
VOLTAGE WAVEFORMS PULSE DURATION



VOLTAGE WAVEFORMS SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

A. C_L includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.

C. All input pulses are supplied by generators having the following characteristics: PRR ⩽ 1 MHz, Z_O = 50 Ω, t_r ⩽ 3 ns, t_f ⩽ 3 ns.

D. The outputs are measured one at a time, with one input transition per measurement.

图 7-1. Load Circuit and Voltage Waveforms

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND
Open Drain	V_{CC}

8 Detailed Description

8.1 Overview

The SN74AHCT244 is organized as two 4-bit buffers/line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ shall be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram

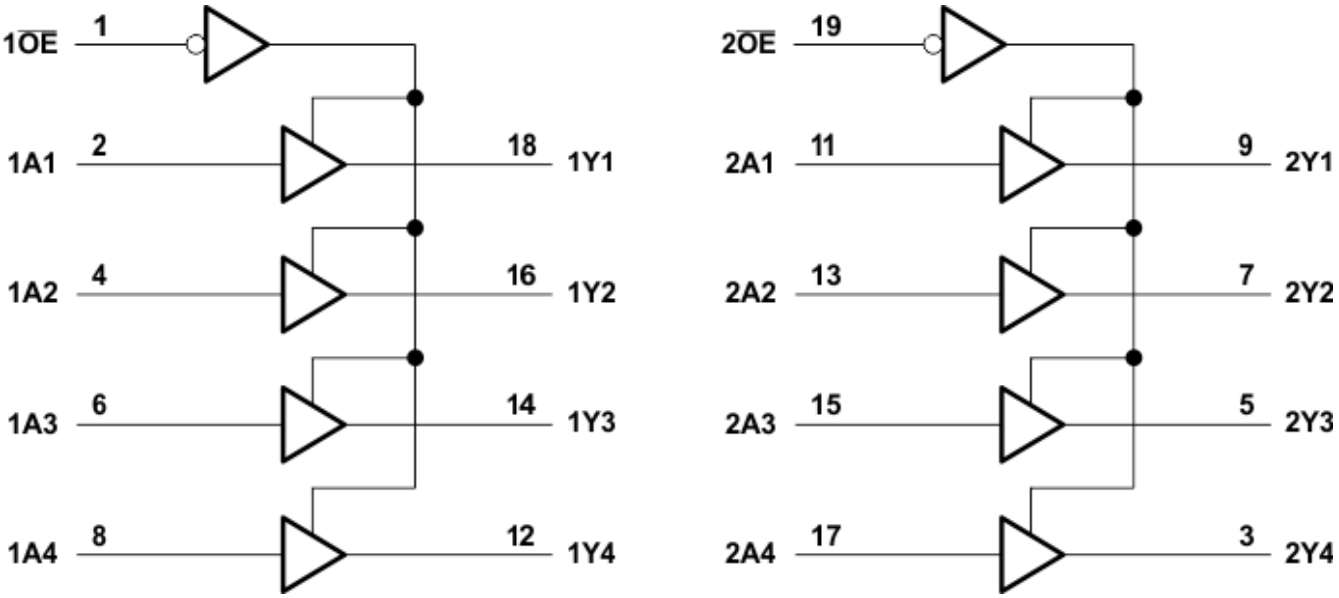


图 8-1. Logic Diagram (Positive Logic)

8.3 Device Functional Mode

表 8-1. (Each 4-Bit Buffer/Driver)

INPUTS		OUTPUT Y
$\overline{OE}$	A	
L	H	H
L	L	L
H	X	Z

9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the 节 6.3 table.

Each VCC pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 μf is recommended; if there are multiple VCC pins, then 0.01 μf or 0.022 μf is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 μf and a 1 μf are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

9.2 Layout

9.2.1 Layout Guidelines

When using multiple-bit logic devices, inputs should never float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. 节 9.2.1.1 specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC}, whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the output section of the part when asserted. This will not disable the input section of the I/Os, so they cannot float when disabled.

9.2.1.1 Layout Example

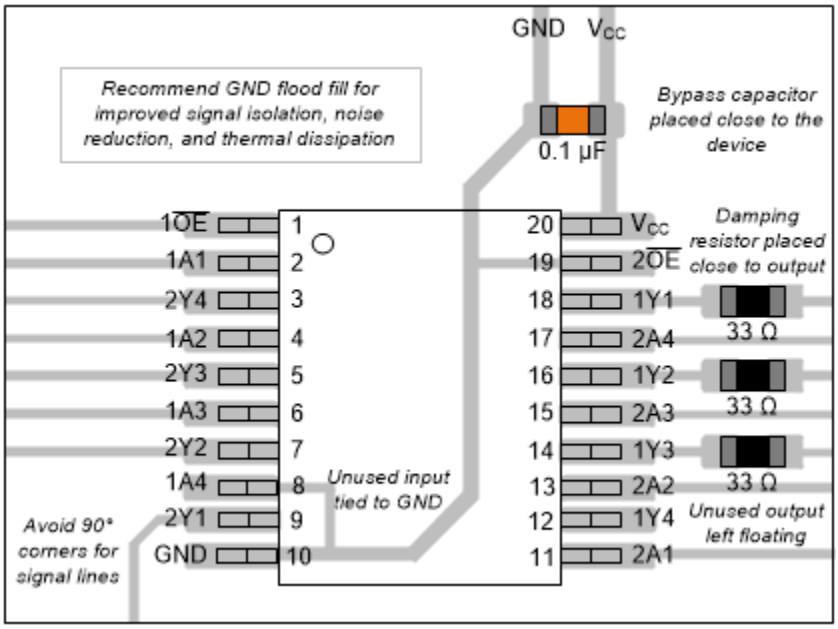


图 9-1. Layout Diagram

10 Device and Documentation Support

10.1 Documentation Support

10.1.1 Related Documentation

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

表 10-1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN74AHCT244-Q1	Click here	Click here	Click here	Click here	Click here

10.2 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.3 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

10.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
所有商标均为其各自所有者的财产。

10.5 静电放电警告

静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

10.6 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CAHCT244IPWRG4Q1	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	AHCT244I	Samples
CAHCT244QDWRG4Q1	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHCT244Q	Samples
CAHCT244QPWRG4Q1	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHCT244Q	Samples
SN74AHCT244IPWRQ1	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	AHCT244I	Samples
SN74AHCT244QDWRQ1	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHCT244Q	Samples
SN74AHCT244QPWRQ1	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHCT244Q	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF SN74AHCT244-Q1 :

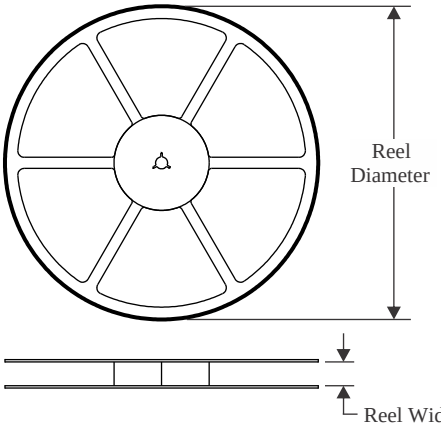
- Catalog : SN74AHCT244
- Enhanced Product : SN74AHCT244-EP
- Military : SN54AHCT244

NOTE: Qualified Version Definitions:

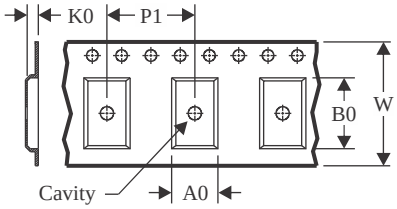
- Catalog - TI's standard catalog product
- Enhanced Product - Supports Defense, Aerospace and Medical Applications
- Military - QML certified for Military and Defense Applications

TAPE AND REEL INFORMATION

REEL DIMENSIONS

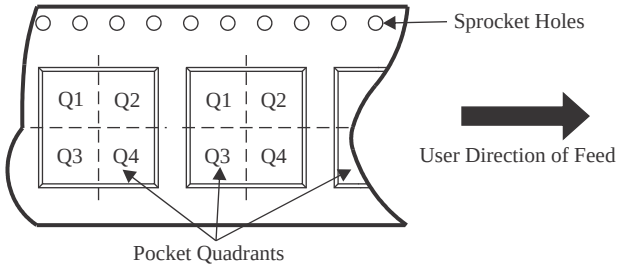


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

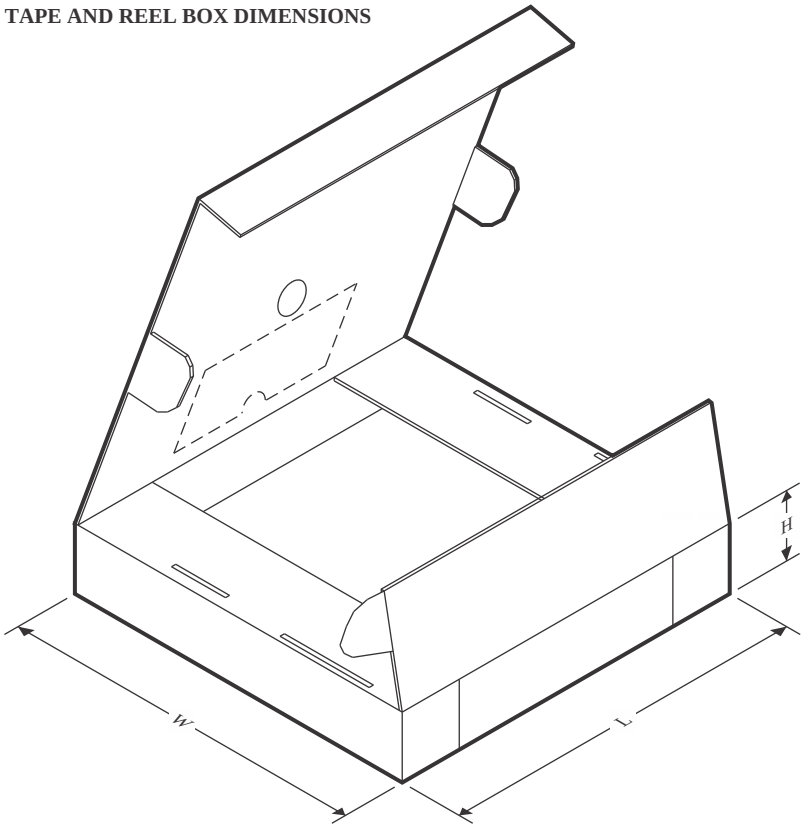
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CAHCT244IPWRG4Q1	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
CAHCT244QDWRG4Q1	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
CAHCT244QPWRG4Q1	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74AHCT244IPWRQ1	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN74AHCT244QDWRQ1	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74AHCT244QPWRQ1	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

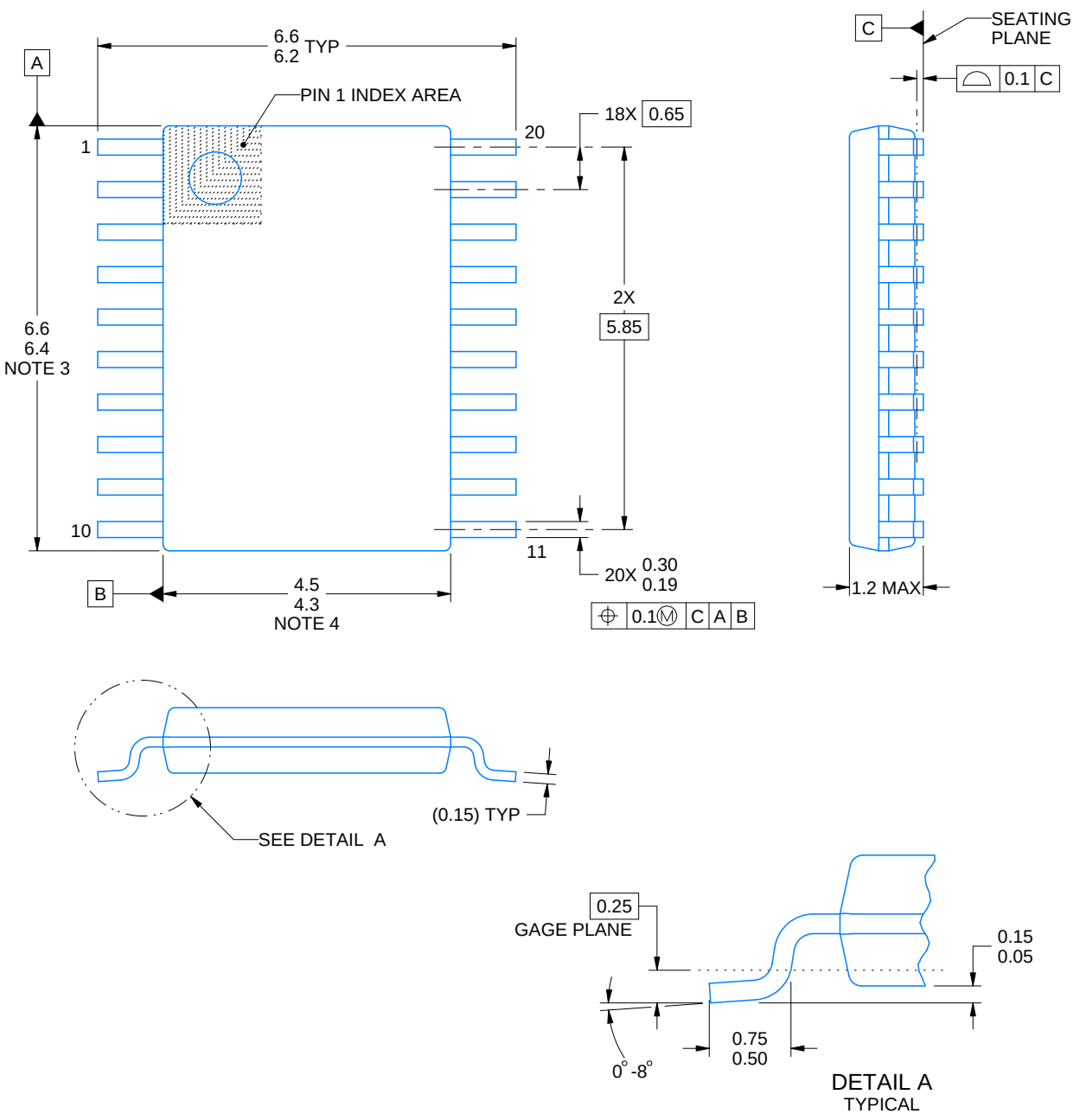
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CAHCT244IPWRG4Q1	TSSOP	PW	20	2000	356.0	356.0	35.0
CAHCT244QDWRG4Q1	SOIC	DW	20	2000	367.0	367.0	45.0
CAHCT244QPWRG4Q1	TSSOP	PW	20	2000	356.0	356.0	35.0
SN74AHCT244IPWRQ1	TSSOP	PW	20	2000	356.0	356.0	35.0
SN74AHCT244QDWRQ1	SOIC	DW	20	2000	367.0	367.0	45.0
SN74AHCT244QPWRQ1	TSSOP	PW	20	2000	356.0	356.0	35.0

PACKAGE OUTLINE

PW0020A

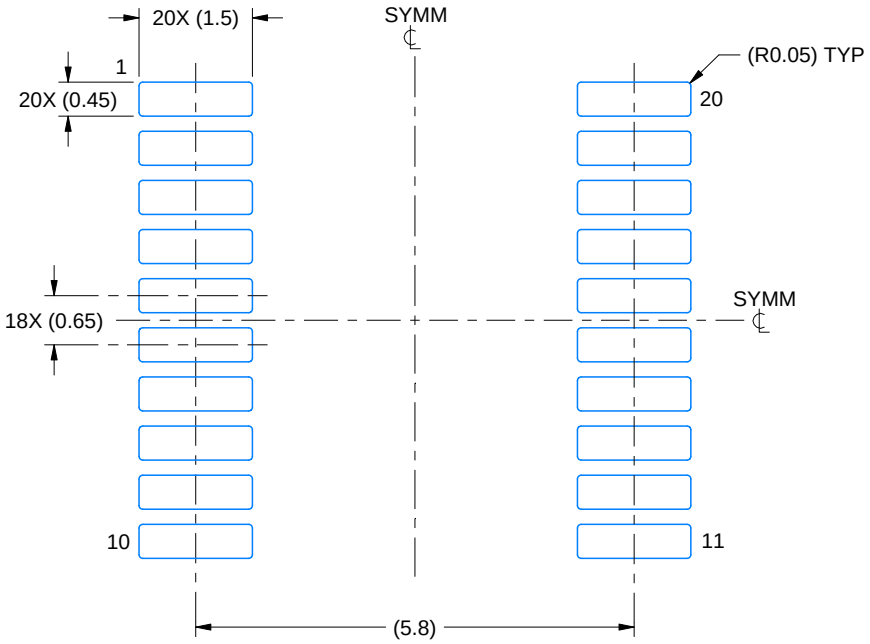
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



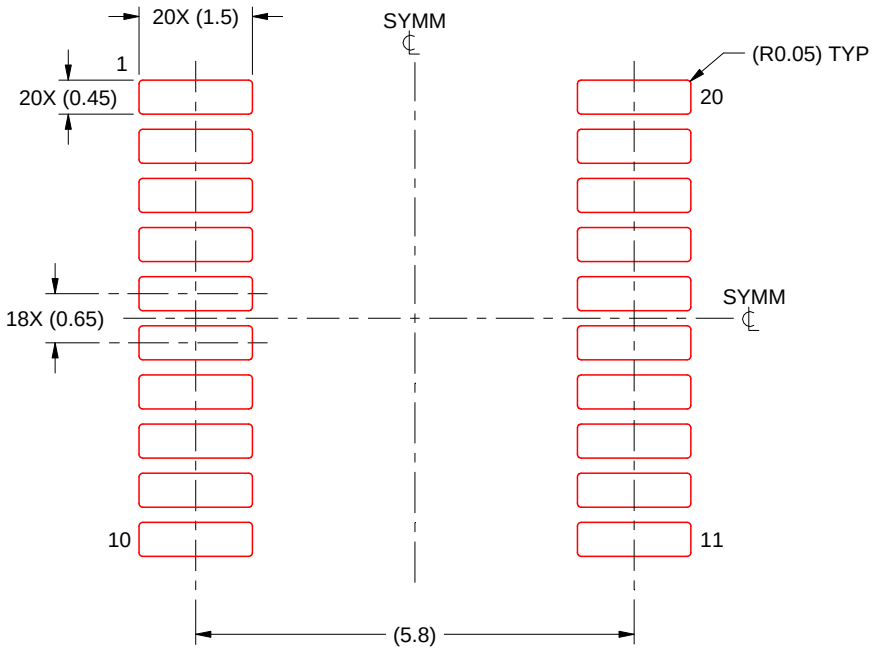
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK DETAILS

4220206/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



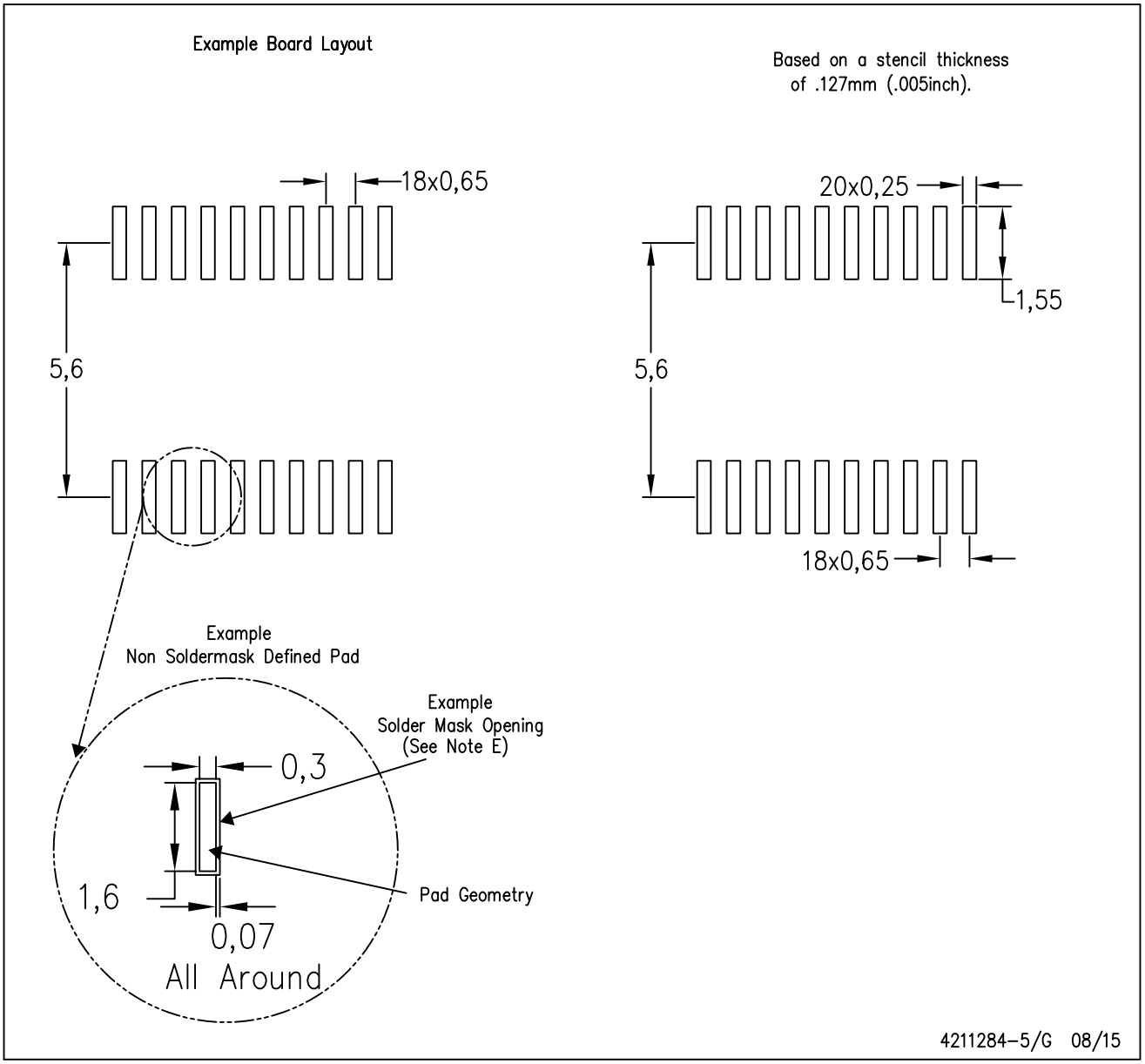
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220206/A 02/2017

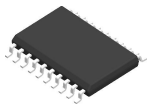
NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PW (R–PDSO–G20) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

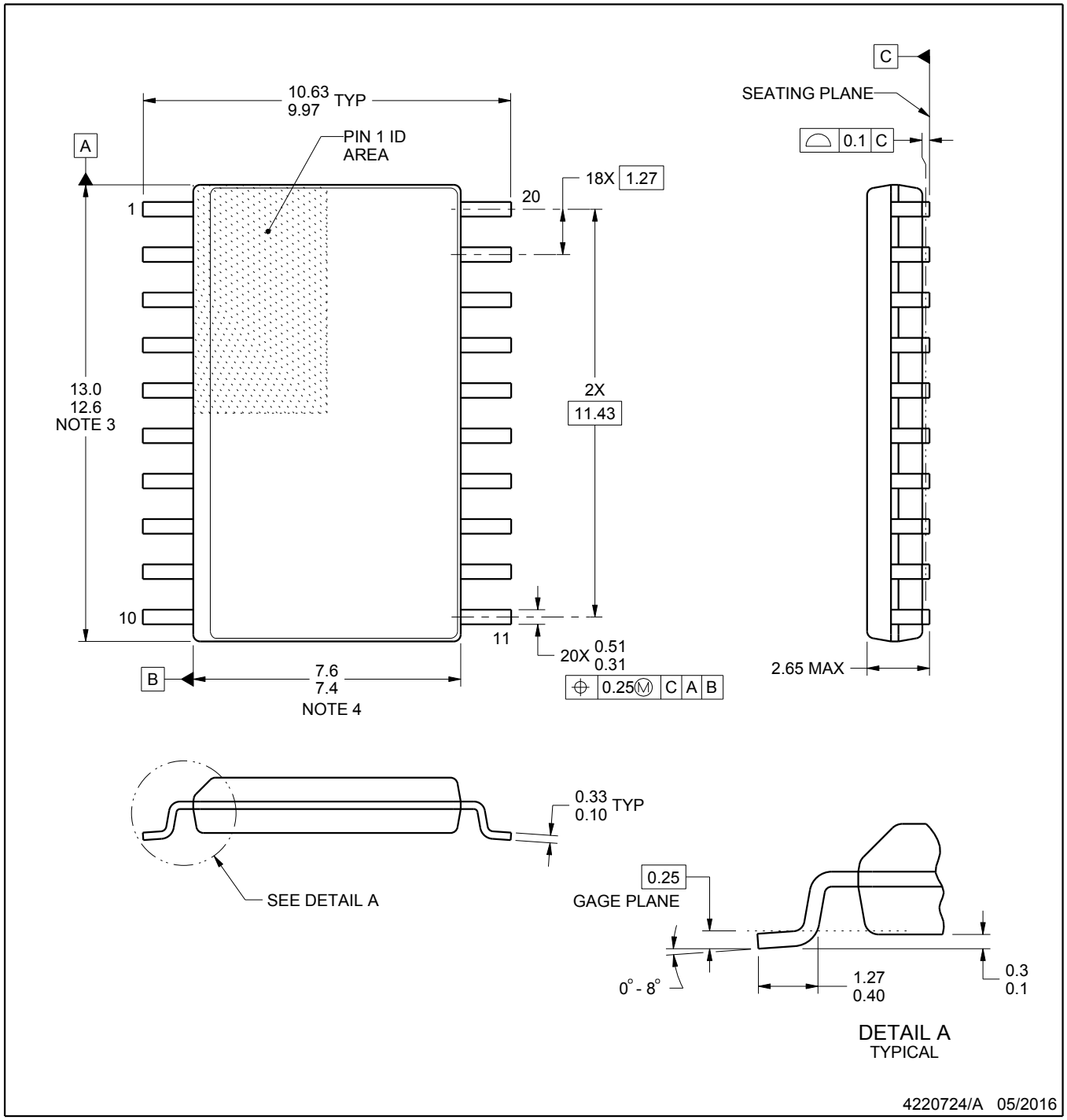


PACKAGE OUTLINE

DW0020A

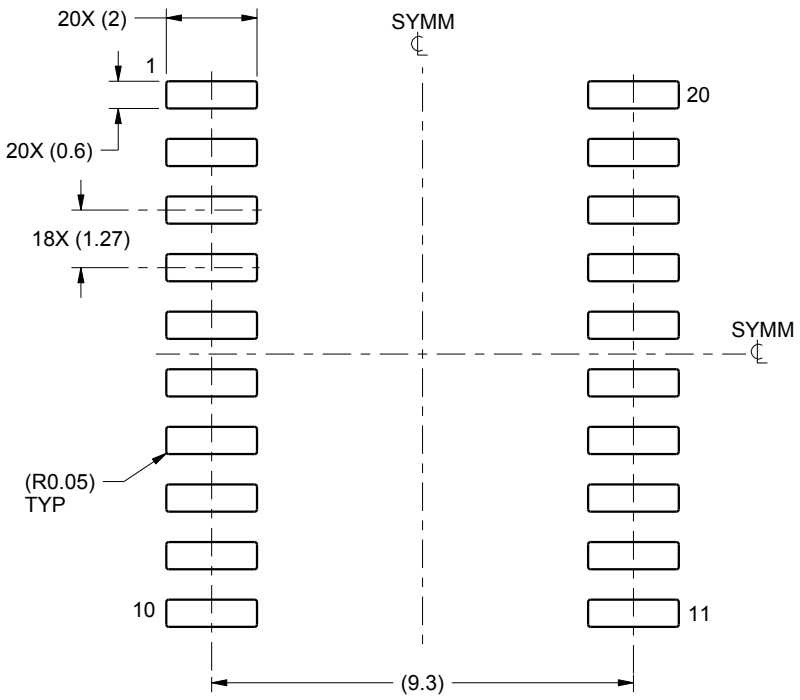
SOIC - 2.65 mm max height

SOIC

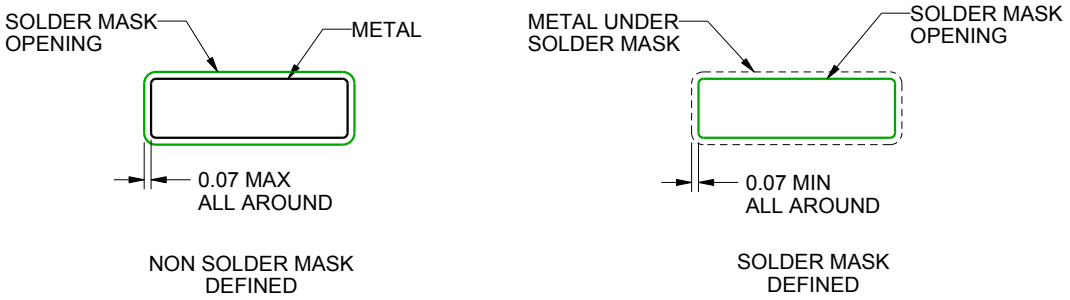


NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.



LAND PATTERN EXAMPLE
SCALE:6X

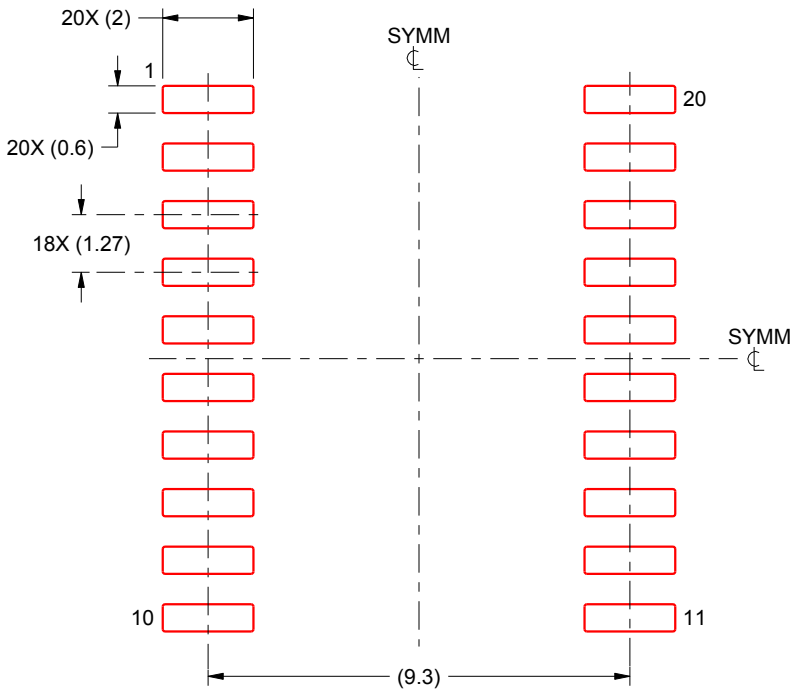


SOLDER MASK DETAILS

4220724/A 05/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

4220724/A 05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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